

EAST Search History**EAST Search History (Prior Art)**

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S14	1	10/574880	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/13 12:09
S16	85	gate with (heat\$3 anneal \$3 fusing weld\$3) with (nano\$1particles (quantum near dots) nano \$1dots nano\$1clusters nano\$1structures)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/13 12:11
S15	218	gate same (heat\$3 anneal \$3 fusing weld\$3) same (nano\$1particles (quantum near dots) nano \$1dots nano\$1clusters nano\$1structures)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/13 12:11
S17	86	gate with (heat\$3 anneal \$3 fus\$3 weld\$3) with (nano\$1particles (quantum near dots) nano \$1dots nano\$1clusters nano\$1structures)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/13 12:18
S18	27	("20020044111" "20020074547" "20020100908" "20020179906" "20030054653" "20030134519" "20040147113" "20050074963" "20060073667" "20070051958" "5947783" "5989945" "6291136" "6294401" "6593591" "6849308"). PN.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/13 12:20
S19	4	(("20020179906") or ("5947783")).PN.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/07/13 13:09

S20	2	("6323143").PN.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/07/13 13:39
S22	1957	(TFT (thin near film near transistor)) same (gate with ((silicon adj nitride) SiN "Si.sub.3N.sub.4" Si3N4 (silicon adj nitride adj oxide) (silicon adj nitride-oxide)) with ((silicon adj oxide) (silicon adj dioxide) "SiO.sub.2" SiO SiO2))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/13 13:42
S21	6190	(TFT (thin near film near transistor)) same ((silicon adj nitride) SiN "Si.sub.3N.sub.4" Si3N4 (silicon adj nitride adj oxide) (silicon adj nitride-oxide)) same ((silicon adj oxide) (silicon adj dioxide) "SiO.sub.2" SiO SiO2)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/13 13:42
S24	4	S22 and S23	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/13 13:44
S23	1796	(257/324,326).CCLS.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/07/13 13:44
S25	14	("4990365" "5232862" "5247190" "5324690" "5373171" "5399502" "5536360" "5643826" "5756250" "5923962" "6144094" "6177323").PN. OR ("6891236").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/07/13 13:49
S26	2	("20050023579").PN.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/07/13 13:51

S28	25	("20010034088" "20020053881" "20020089616" "20020136829" "20030083203" "20030143794" "20030219934" "20040038138" "20040113161" "20050054181" "20050250262" "5883682" "6416583" "6426595" "6555420" "6587165" "6627263" "6630274" "6787407" "6821827" "6891236" "6908796" "6911675" "6952036" "6994414"). PN. OR ("7223641"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/07/13 13:52
S27	2	("20050214983").PN.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/07/13 13:52
S29	39	("20010034088" "20020053881" "20020089616" "20020136829" "20030083203" "20030143794" "20030219934" "20040038138" "20040113161" "20050054181" "20050250262" "5883682" "6416583" "6426595" "6555420" "6587165" "6627263" "6630274" "6787407" "6821827" "6891236" "6908796" "6911675" "6952036" "6994414"). PN. OR ("7223641"). URPN.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/13 14:01
S30	2	09/479262	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/13 14:02
S31	3	("2005/0074963").URPN.	USPAT	OR	ON	2009/07/13 14:38

EAST Search History (Interference)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L17	546	(pixel and ((thin adj film adj transistor) TFT) and gate and ((silicon adj nitride) SiN "Si.sub.3N. sub.4" Si3N4 (silicon adj nitride adj oxide) (silicon adj nitride-oxide)) and ((silicon adj oxide) (silicon adj dioxide) "SiO.sub.2" SiO SiO2)).clm.	US-PGPUB; USPAT	OR	ON	2009/07/14 10:23
L19	1	(pixel and (light light \$emi\$5) and ((thin adj film adj transistor) TFT) and gate and fus\$4 and ((silicon adj nitride) SiN "Si. sub.3N.sub.4" Si3N4 (silicon adj nitride adj oxide) (silicon adj nitride-oxide)) and ((silicon adj oxide) (silicon adj dioxide) "SiO.sub.2" SiO SiO2)).clm.	US-PGPUB; USPAT	OR	ON	2009/07/14 10:24
L18	157	(pixel and (light light \$emi\$5) and ((thin adj film adj transistor) TFT) and gate and ((silicon adj nitride) SiN "Si.sub.3N. sub.4" Si3N4 (silicon adj nitride adj oxide) (silicon adj nitride-oxide)) and ((silicon adj oxide) (silicon adj dioxide) "SiO.sub.2" SiO SiO2)).clm.	US-PGPUB; USPAT	OR	ON	2009/07/14 10:24

7/14/2009 10:28:06 AM

C:\Documents and Settings\ETaylor\My Documents\EAST\Workspaces\10574880 Light Emitting Device.wsp